QCCVO.

QPA9901 2110-2200MHz 4 W High-Efficiency Amplifier

Product Overview

The QPA9901 is a high-efficiency, linearizable power amplifier targeting Band 66 along with Band 1 small-cell wireless infrastructure systems. The product delivers high efficiency of 32% at +28dBm average output power, while providing excellent DPD linearized ACPR of -48dBc for signal bandwidths of up to 60MHz.

The QPA9901 is housed in a 5x5mm SMT package. It is pin-to-pin compatible to QPA9903 (band 3 high-efficiency small cell PA).



16 Pad 5 x 5 mm Package

Key Features

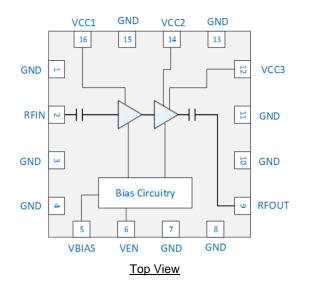
- 2110-2200MHz
- Up to 60MHz IBW capability
- 36.5dB Gain typical
- 32% PAE at +28dBm power output
- <-48dBc ACPR DPD linearized at +28dBm Pout
- 1.8V logic compatible PA ON/OFF control
- On chip ESD protection

Applications

- 3GPP Band 66 along with Band 1 Small Cells
- M-MIMO
- Repeaters / DAS
- Mobile Infrastructure
- General Purpose Wireless

Part No.	Description
QPA9901TR13	2500 on reel
QPA9901EVB-01	2110-2200 MHz EVB

Functional Block Diagram



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Absolute Maximum Ratings

Parameter	Rating
Storage Temperature	−55 to +125 °C
RF Input Power, Pulsed CW, 50 $\Omega^{(1)}$	+10 dBm
Device Voltage (Vcc)	+5.5 V

Exceeding any one or a combination of the Absolute Maximum Ra conditions may cause permanent damage to the device. Extenapplication of Absolute Maximum Rating conditions to the device may red device reliability. Note:

1. 2110-2200 MHz, Pulsed CW, 10% duty cycle, 100us period.

Recommended Operating Conditions

Parameter	Min	Тур	Мах	Units
Device Voltage (Vcc)	+4.75	+5	+5.25	V
TCASE	-40		+85	°C
Tj for >10 ⁶ hours MTTF			+175	°C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

Parameter	Conditions ⁽¹⁾	Min	Тур	Max	Units
Operational Frequency Range		2110		2200	MHz
Test Frequency			2140		MHz
Gain	Pout = +28 dBm	34	36.5		dB
Input Return Loss			-13		dB
Output P3dB	100 µs/1 ms, 10% duty cycle	35	+35.6		dBm
Power Added Efficiency (2)	Pout = +28 dBm	29	32		%
ACPR(Uncorrected) ⁽²⁾	Pout = +28 dBm		-38	-34	dBc
ACPR(Uncorrected) ⁽³⁾	Pout = +28 dBm		-33		dBc
ACPR(Corrected) ⁽²⁾	Pout = +28 dBm		-48		dBc
Quiescent Current, Icq	Pins 12, 14 and 16		93		mA
Total Operating Current	Pins 5, 12, 14 and 16, Pout = +28 dBm		394		mA
Thermal Resistance, θ_{jc}	Junction to case		24.7		°C/W
V _{EN} High		1.17	1.8	Vcc	V
V _{EN} Low		0	0	0.5	V
2nd Harmonic	Pout = +28 dBm		-45		dBc
3rd Harmonic	Pout = +28 dBm		-60		dBc

Notes:

1. Test conditions unless otherwise noted: All V_{CC} & V_{BIAS} = +5.0 V, V_{EN} = +1.8 V, Temp = +25 °C, 50 Ω system.

2. LTE, 20 MHz E-UTRA Test Model 1.1 or 3.1, PAR = 8.5 dB at 0.01% Probability

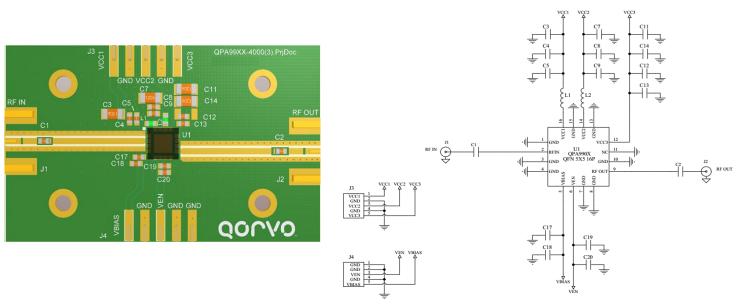
3. LTE, 20 MHz x 3 E-UTRA Test Model 1.1 or 3.1, PAR = 8.5 dB at 0.01% Probability

Power Amplifier Enable Logic Table

Parameter	High	Low
VEN	Power Amplifier ON	Power Amplifier OFF

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2110–2200 MHz Evaluation Board



Notes:

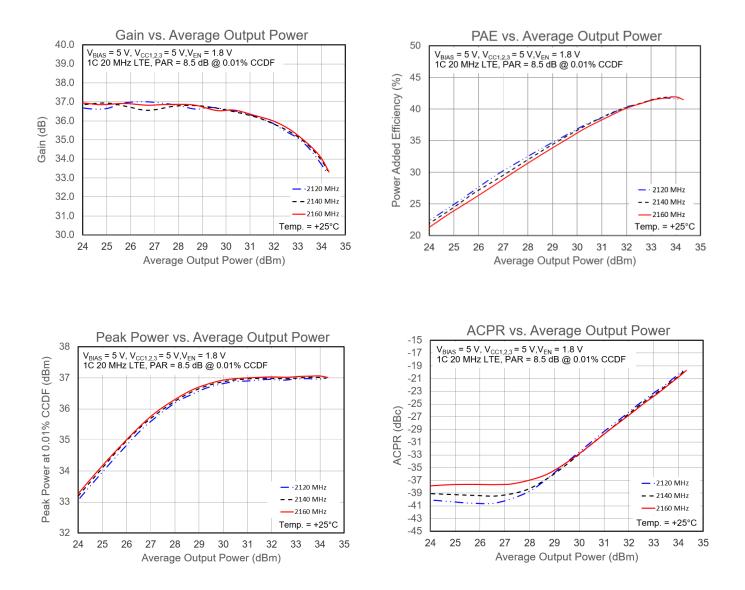
1. See Evaluation Board PCB Information for material and stack up.

Bill of Material – QPA9901EVB01

Reference Des.	Value	Description	Manuf.	Part Number
U1	-	Amplifier, QPA9901 2110-2200 MHz, High-Efficiency	Qorvo	QPA9901
C1, C2	100 pF	CAP,100 pF, 0603, 5%, 50V, NPO	various	
C5, C9, C13, C17, C19	1000 pF	CAP,1000 pF, 0603, 5%, 50V, NPO	various	
C4, C8, C12, C18, C20	0.1 µF	CAP,0.1 µF, 0603, 10%, 50V, X7R	various	
C3, C7, C14	10 µF	CAP, 10 μF, 1206, 16V	various	
L1, L2	0 Ω	RES 0 Ω, 0603, 1/16W, Chip	various	

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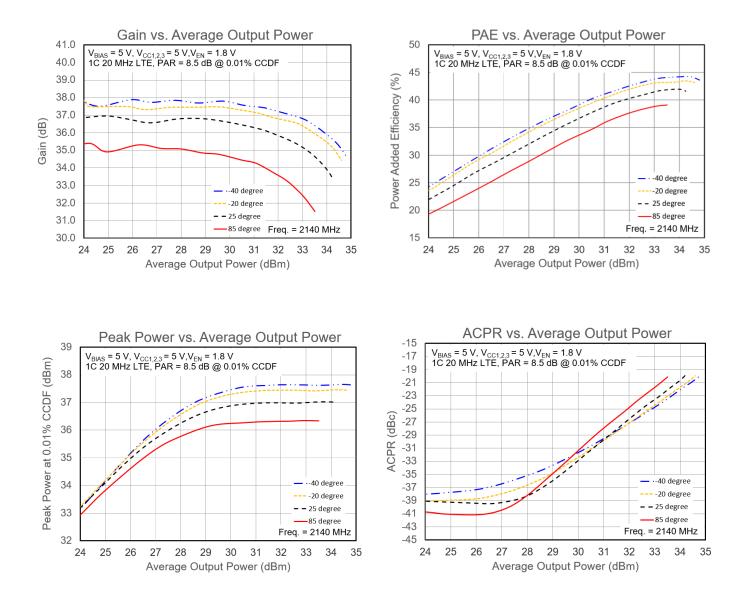
Performance Plots – LTE, Over Frequency



Test conditions unless otherwise noted: $V_{BIAS} = 5 V$, $V_{CC1,2,3} = 5 V$, $V_{EN} = 1.8 V$, $T = +25^{\circ}C$, tested using a single-carrier, 20 MHz LTE signal with 8.5 dB PAR at 0.01% CCDF on a reference design fixture.

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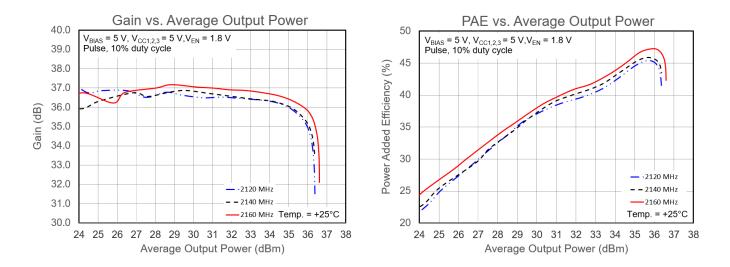
Performance Plots – LTE, Over Temperature



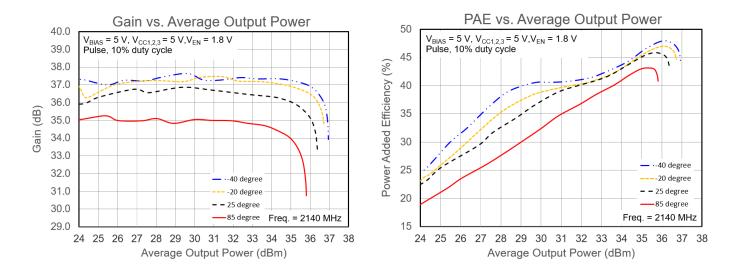
Test conditions unless otherwise noted: V_{BIAS} = 5 V, V_{CC1.2.3} = 5 V, V_{EN} = 1.8 V, tested at 2140 MHz using a single-carrier, 20 MHz LTE signal with 8.5 dB PAR at 0.01% CCDF on a reference design fixture.

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Performance Plots – Pulse Signal Measurements, Frequency and Temperature



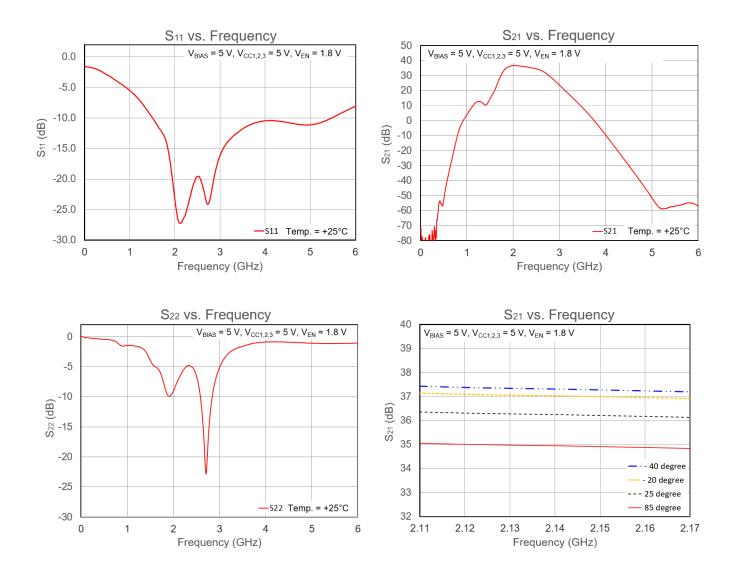
Test conditions unless otherwise noted: $V_{BIAS} = 5 V$, $V_{CC1,2,3} = 5 V$, $V_{EN} = 1.8 V$, $T = +25^{\circ}C$, tested using a pulse signal, 10% duty cycle.



Test conditions unless otherwise noted: V_{BIAS} = 5 V, V_{CC1,2,3} = 5 V, V_{EN} = 1.8 V, tested at 2140 MHz using a pulse signal, 10% duty cycle.

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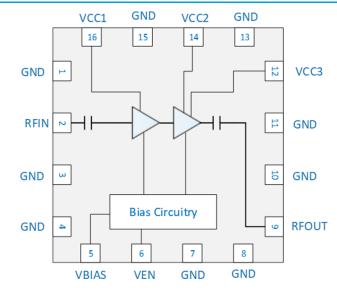
Performance Plots – S-parameter



Test conditions unless otherwise noted: $V_{BIAS} = 5 V$, $V_{CC1,2,3} = 5 V$, $V_{EN} = 1.8 V$.

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Pad Configuration and Description



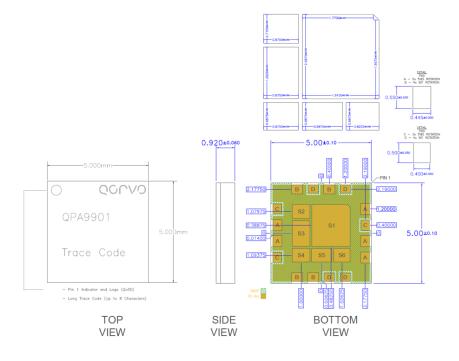
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Pad No.	Label	Description	
1, 3, 4, 7, 8, 10, 11, 13, 15	GND	Ground connection.	
2	RFIN	RF input, internally matched to 50Ω .	
5	VBIAS	Bias circuit supply voltage	
6	V _{EN}	Amplifier enable voltage (regulated internally)	
9	RFout	RF output, internally matched to 50Ω . It has low impedance at DC. An external series capacitor is required if high impedance is needed at DC.	
12	Vcc ₃	Supply voltage for the various amplifier stages	
14	Vcc2	Supply voltage for the various amplifier stages	
16	Vcc1	Driver stage supply voltage	
Backside Paddle	GND	Ground connection. The back side of the package should be connected to the ground plan though as short of a connection as possible. PCB via holes under the device are recommended.	

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Package Marking and Dimensions

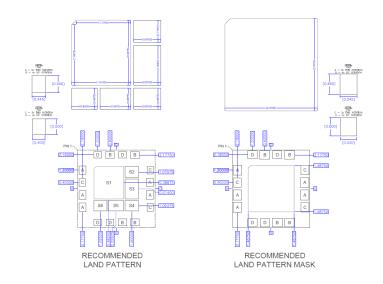
Marking: Pin 1 Indicator and Qorvo Logo



Notes:

- 1. All dimensions are in millimeters. Angles are in degrees.
- 2. The terminal #1 identifier and terminal numbering conform to JESD 95-1 SPP-012.
- 3. Contact plating: ENEPIG (Electroless Nickel Electroless Palladium Immersion Gold)

PCB Mounting Pattern



QONOD

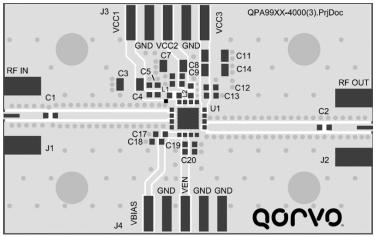
Evaluation Board PCB Information

PC Board Layout

Layer	Name	Material	Thickness	Constant
1	Top Overlay			
2	Top Solder	Solder Resist	0.40 mil	3.5
3	Top Layer	Copper	1.40 mil	
4	Dielectric1	RO4350	20.00 mil	3.48
5	Bottom Layer	Copper	1.40 mil	

PCB Material (stackup)

Total thickness: 23.2mill



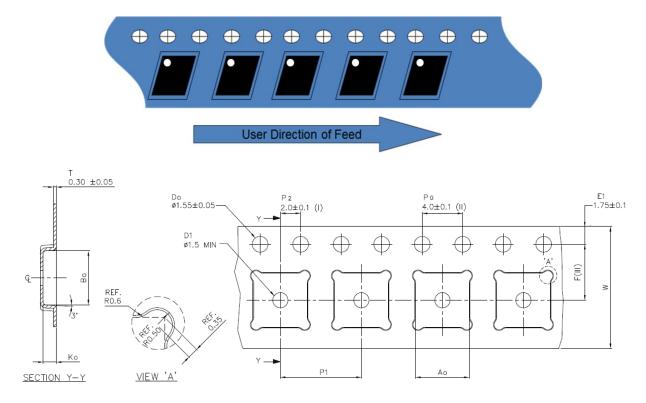
Notes:

- 1. All dimensions are in millimeters. Angles are in degrees.
- 2. Use 1 oz. copper minimum for top and bottom layer metal.
- 3. Via holes are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. We recommend a 0.35mm (#80/.0135") diameter bit for drilling via holes and a final plated thru diameter of 0.25 mm (0.10").
- 4. Ensure good package backside paddle solder attach for reliable operation and best electrical performance.

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Tape and Reel Information – Carrier and Cover Tape Dimensions

Tape and reel specifications for this part are also available on the Qorvo website. Standard T/R size = 2500 pieces on a 13° reel.

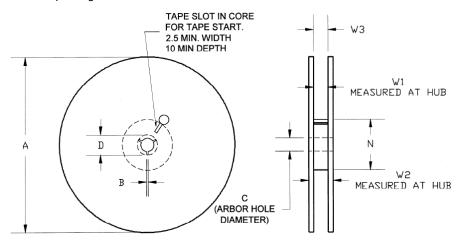


Feature	Measure	Symbol	Size (in)	Size (mm)
	Length	A0	0.209	5.3
Covity	Width	B0	0.209	5.3
Cavity	Depth	K0	0.051	1.3
	Pitch	P1	0.315	8.0
Centerline Distance	Cavity to Perforation - Length Direction	P2	0.079	2.0
Centenine Distance	Cavity to Perforation - Width Direction	F	0.217	5.5
Cover Tape	Width	С	0.362	9.2
Carrier Tape	Width	W	0.472	12

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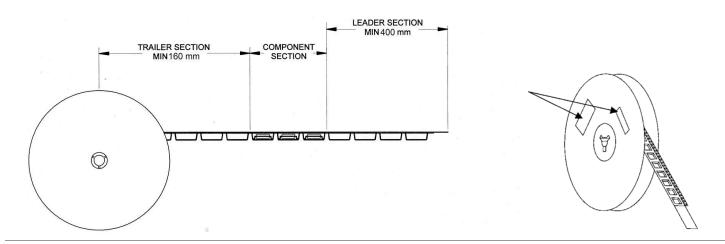
Tape and Reel Information – Reel Dimensions

Packaging reels are used to prevent damage to devices during shipping and storage, loaded carrier tape is typically wound onto a plastic take-up reel. The reel size is 13" diameter. The reels are made from high-impact injection-molded polystyrene (HIPS), which offers mechanical and ESD protection to packaged devices.



Feature	Measure	Symbol	Size (in)	Size (mm)
	Diameter	A	12.992	330.00
Flange	Thickness	W2	0.717	18.20
	Space Between Flange	W1	0.504	12.80
Hub	Outer Diameter	N	4.016	102.00
	Arbor Hole Diameter	С	0.512	13.00
	Key Slit Width	В	0.079	2.00
	Key Slit Diameter	D	0.795	20.2

Tape and Reel Information – Tape Length and Label Placement

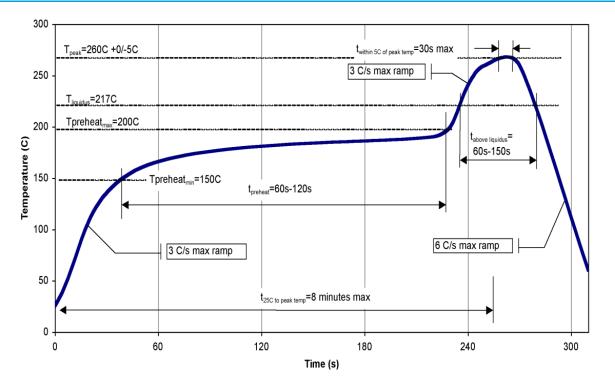


Notes:

- 1. Empty part cavities at the trailing and leading ends are sealed with cover tape. See EIA 481.
- 2. Labels are placed on the flange opposite the sprockets in the carrier tape.

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Recommended Solder Temperature Profile



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Handling Precautions

Parameter	Rating	Standard	
ESD-Human Body Model (HBM)	1C	ESDA/JEDEC JS-001-2012	Caution! ESD-Sensitive Device
ESD-Charged Device Model (CDM)	C3	JEDEC JESD22-C101F	
MSL-Moisture Sensitivity Level	3	IPC/JEDEC J-STD-020	

Solderability

Compatible with both lead-free (260°C max. reflow temp.) and tin/lead (245°C max. reflow temp.) soldering processes. Solder profiles available upon request.

Contact plating: ENEPIG (Electroless Nickel Electroless Palladium Immersion Gold)

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Product uses RoHS Exemption 7c-I to meet RoHS Compliance requirements.
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C15H12Br402) Free
- PFOS Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.qorvo.com

Tel: 1-844-890-8163

Email: <u>customer.support@qorvo.com</u>

For technical questions and application information:

Email: appsupport@gorvo.com

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